

## WEJ<sup>®</sup>

## MBR1030CT-MBR1060CT

SCHOTTKY BARRIER RECTIFIER

## FEATURES

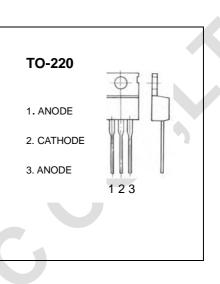
- · Schottky Barrier Chip
- $\cdot$  Guard Ring Die Construction for Transient Protection
- · Low Power Loss, High Efficiency
- · High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- $\cdot$  For Use in Low Voltage, High Frequency Inverters, Free

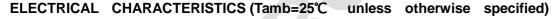
1 0-

2 °

3 0

Wheeling, and Polarity Protection Applications





Characteristic	Symbol	MBR MBR MBR MBR MBR MBR						
		1030CT	1035CT	1040CT	1045CT	1050CT	1060CT	Unit
		103001	103501	104001	104301	105001	100001	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>							
Working Peak Reverse Voltage	V <sub>RWM</sub>	30	35	40	45	50	60	V
DC Blocking Voltage	VR							
PMS Reverse Voltage	V <sub>R(RMS)</sub>	21	24.5	28	31.5	35	42	V
Average Rectified Output Current	10						•	
(Note 1) @ T <sub>c</sub> =105℃	lo 10						A	
Non-Repetitive Peak Forward Surge Current								
8.3ms Single half sine-wave superimposed on	I <sub>FSM</sub>	125						A
rated load (JEDEC Method)								
Repetitive Peak Reverse Surge Current		4.0						
@ t≤ 2.0µs	I <sub>RRM</sub>	1.0					A	
Forward Voltage Drop @ I <sub>F</sub> =5.0A, T <sub>C</sub> =125℃		0.57 0.70						
@ I <sub>F</sub> =5.0A, T <sub>C</sub> = 25℃	V <sub>FM</sub>	0.70 0.84				0.	80	V
@ I <sub>F</sub> =10A, T <sub>C</sub> = 25℃						0.	95	
Peak Reverse Current @ T <sub>c</sub> = 25℃	0.1							
at Rated DC Blocking Voltage @ T <sub>c</sub> =125℃	I <sub>RM</sub>	15						mA
Typical Junction Capacitance (Note 2)	Cj	150						pF
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150					°C	

Notes: 1. Thermal resistance junction to case mounted heat sink.

2. Measured at 1.OMHz and applied reverse voltage of 4.0V DC.